TO-126F PNP Silicon PNP transistor in a TO-126F Plastic Package.

I_C $V_{CE(sat)}$

High I_C, low $V_{CE(sat)}$.

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Strobe flash applications, audio power amplifier applications.

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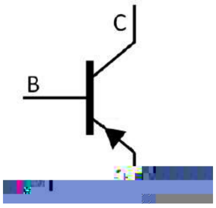
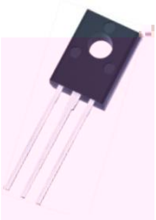
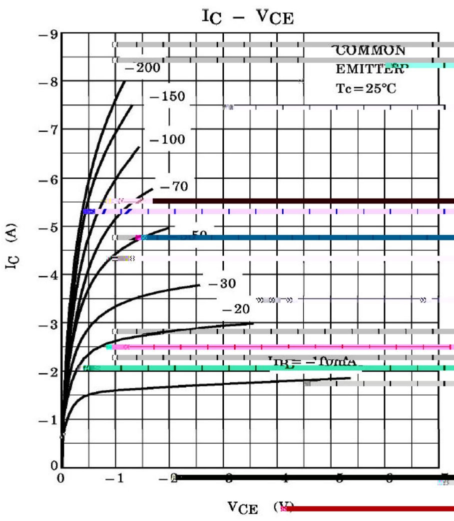


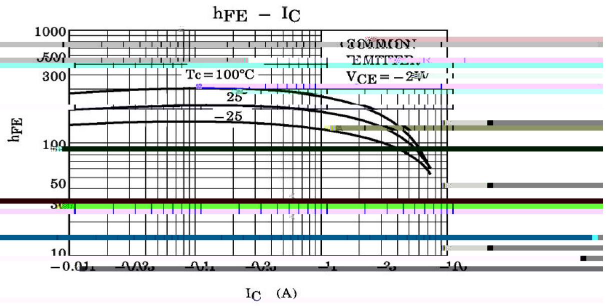


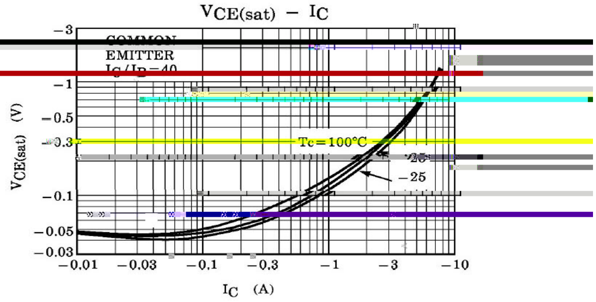
PIN1 Emitter PIN 2 Collector PIN 3 Base

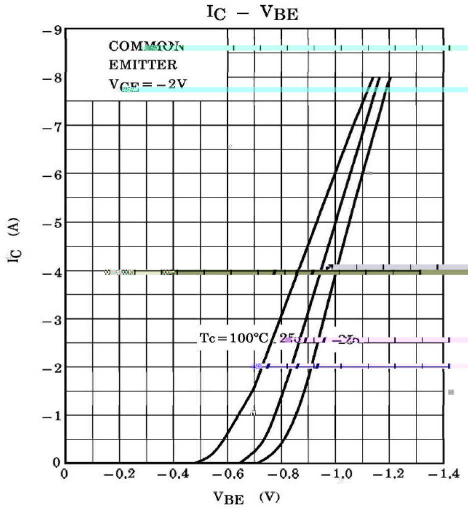
Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	-35	V
Collector to Emitter Voltage	V_{CEO}	-20	V
Emitter to Base Voltage	V_{EBO}	-8.0	V
Collector Current - Continuous	I_C	-5.0	A
Collector Current – Continuous(Pulse)	I_{CP}	-8.0	A
Base Current – Continuous	I_B	-1.0	A
Collector Power Dissipation	P_C	1.5	W
Collector Power Dissipation	$P_C(T_C=25\ )$	10	W
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

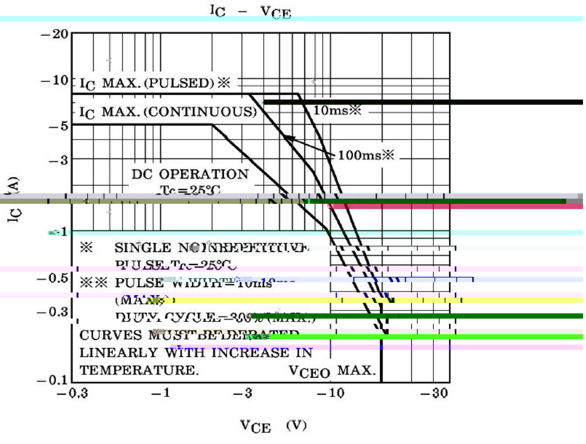
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector to Emitter Breakdown Voltage	V					


IC – VCE
COMMON EMITTER
Tc=25°C
−200
−150
−100
−70
−50
−30
−20
IB=−10mA
IC (A)
−9
−8
−7
−6
−5
−4
−3
−2
−1
0
VCE (V)
0
−1
−2
−3
−4
−5
−6
−7

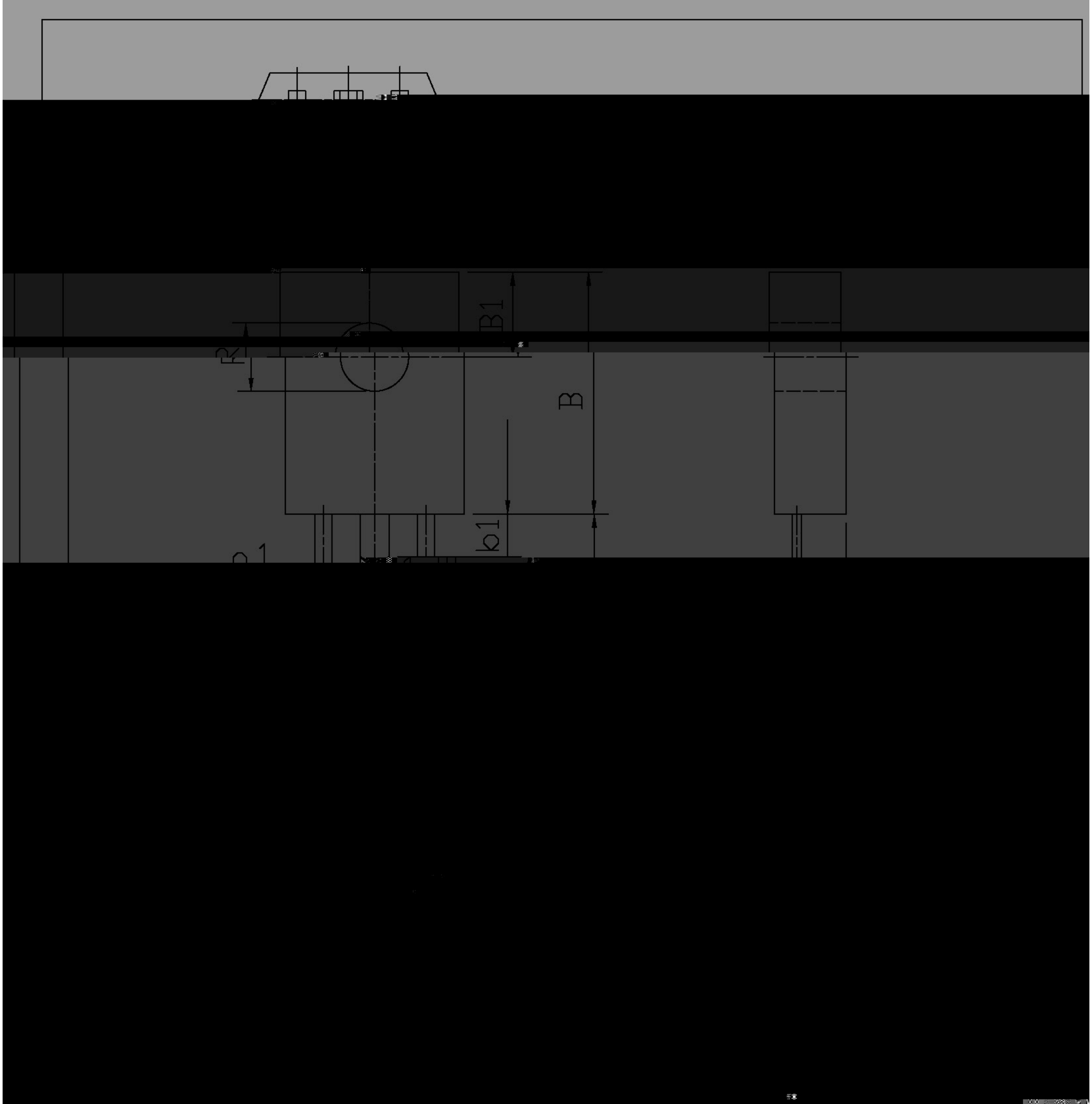

hFE – IC
COMMON EMITTER
VCE=−2V
Tc=100°C
25
−25
hFE
1000
500
300
100
50
30
10
IC (A)
−0.01
−0.03
−0.1
−0.3
−1
−3
−10


VCE(sat) – IC
COMMON EMITTER
IC/IB=40
Tc=100°C
25
−25
VCE(sat) (V)
−3
−1
−0.5
−0.3
−0.1
−0.05
−0.03
IC (A)
−0.01
−0.03
−0.1
−0.3
−1
−3
−10

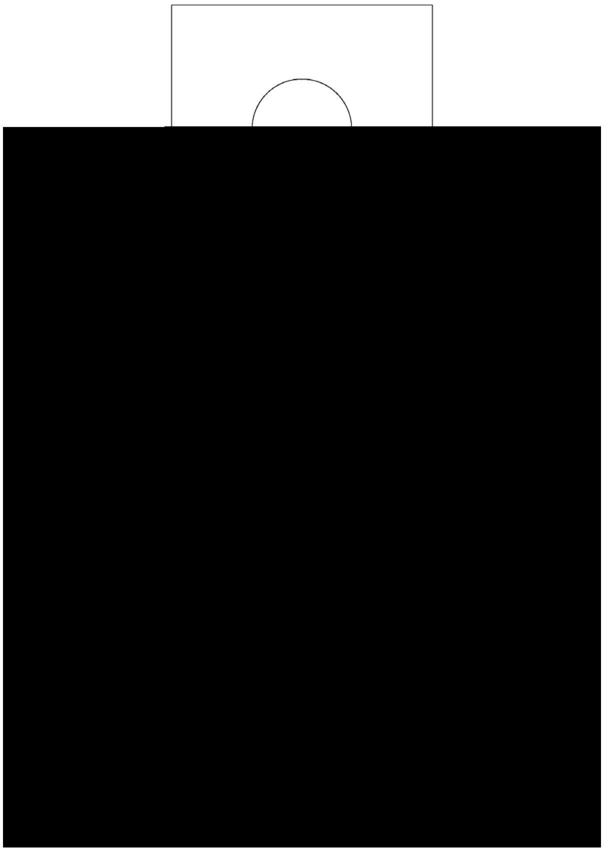

IC – VBE
COMMON EMITTER
VCE=−2V
Tc=100°C
25
−25
IC (A)
−9
−8
−7
−6
−5
−4
−3
−2
−1
0
VBE (V)
0
−0.2
−0.4
−0.6
−0.8
−1.0
−1.2
−1.4


IC – VCE
IC MAX. (PULSED)※
IC MAX. (CONTINUOUS)
10ms※
100ms※
DC OPERATION
Tc=25°C
※ SINGLE NONREPETITIVE PULSE Tc=25°C
※※ PULSE WIDTH=10ms (MAX.)
DUTY CYCLE=30% (MAX.)
CURVES MUST BE DERATED LINEARLY WITH INCREASE IN TEMPERATURE.
VCEO MAX.
IC (A)
−20
−10
−5
−3
−1
−0.5
−0.3
−0.1
VCE (V)
−0.3
−1
−3
−10
−30

TO-126F　　单位：mm



Max	Symbol	Min	Max	Symbol	Min
0.86	A	7.8	8.2	b1	0.66



BR

A1357

O: h_{FE}

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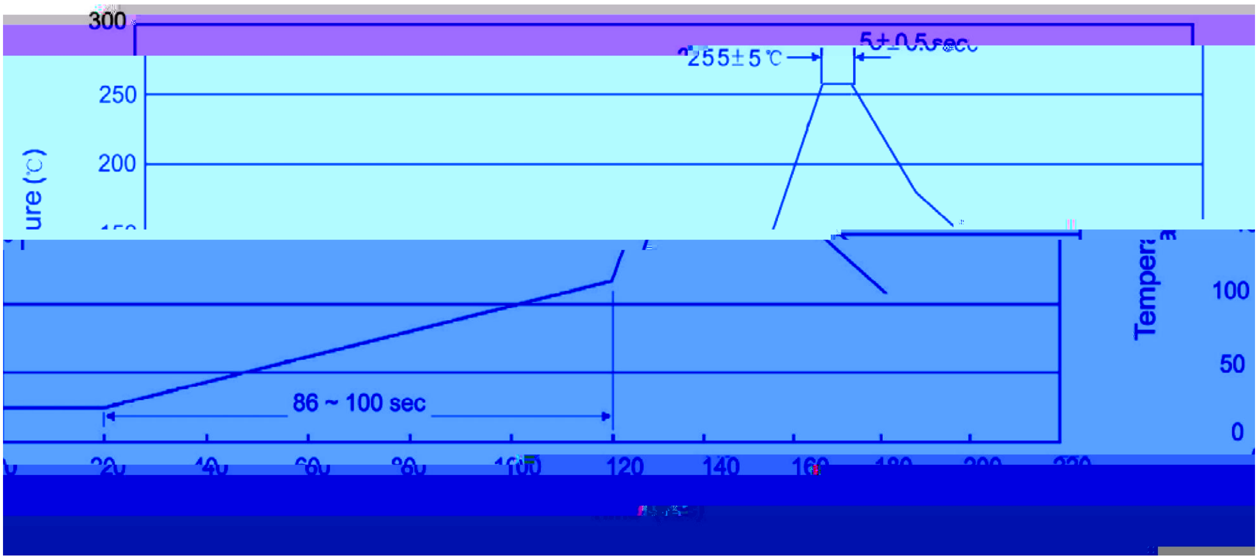
Note:

BR: Company Code

A1357: Product Type.

O: h_{FE} Classifications Symbol

****: Lot No. Code, code change with Lot No.



	Note:
1 25 150 60 90sec;	1.Preheating:25~150 , Time:60~90sec.
2 255±5 5±0.5sec;	2.Peak Temp.:255±5 , Duration:5±0.5sec.
3 2 10 /sec.	3. Cooling Speed: 2~10 /sec.

255±

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